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In re Application of:

Hytros, et al.

Serial No.: 10/033,544

Confirmation No.: 7363

Filed:

December 27, 2001

For:

Dual-Gas Delivery System

for Chemical Vapor Deposition Processes

Commissioner for Patents Washington, D.C. 20231

Dear Sir:

Group Art Unit:

Examiner:

to be assigned

CERTIFICATE OF MAILING

37 CFR 1.8

I hereby certify that this correspondence is being deposited on April 18, 2002 with the United States Postal Service as First Class Mail in an envelope addressed to: Assistant Commissioner for Patents, Washington, D.C. 20231.

4/18/02

Signature

INFORMATION DISCLOSURE STATEMENT

The Applicants, and the Attorney who signs below on the basis of the information supplied by the inventor and the information in his file, submit herewith patents, publications, or other information of which they are aware, which may be material to the examination of this application and in respect of which there may be a duty to disclose in accordance with 37 CFR § 1.56.

While the information submitted in this Information Disclosure Statement may be material pursuant to 37 CFR § 1.56, it is not intended to constitute an admission that any patent, publication, or other information referred to therein is prior art for this invention unless specifically designated as such.

In accordance with 37 CFR § 1.97, this Information Disclosure Statement is not to be construed as a representation that a search has been made or that no other possibly material information as defined under 37 CFR § 1.56(a) exists.

The patents and/or publications submitted herewith are set forth on the attached Form PTO-1449.

Applicant believes that no fee is due as a result of this filing. However, If the Commissioner deems that fees are due under 37 CFR § 1.17(p) pursuant to § 1.97, he is hereby authorized to charge this fee, and any other fee necessary to make this submission timely, to Deposit Account No. 20-0782/AMAT 6551/CMI/TICL/RKK.

Respectfully submitted,

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Sheet 1 of 1 sheet(s)

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U.S. Department of Commerce, Patent and Trademark Office					Docket No.		Serial No.		
(PTO Form 1449 modified)					AMAT/6551/CMI/TICL/ RKK		10/033,544		
INFORMATION DISCLOSURE SEAVEMENTS APPLICATION						Applicant		Confirmation No.:	
						Hytros, et al.		7363	
(Use several sheets if necessary)					Filing Date		Group		
Examiner:						December 27, 2001		Unknown	
U.S. Patent	Docum			, , , , , , , , , , , , , , , , , , , ,	<u> </u>				
*Examiner Initial		Document Number	Issue Date	Applicant(s) Name	Class	Subclass	Filing Date If Appropriate		
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	C5								
Examiner	-				Date Cons	idered			
*EXAMINER: conformance	Initial if	reference considered considered. Include	, whether or not citati copy of this form with	on is in conformance your communication	with MPEP 60 to applicant.	9; Draw line th	rough citation if	not in	